

ab which is electrically connected to either one of said power supply connection pads or one of said ground line connection pads, respectively; and

capacitors electrically connected to at least one surface of said conductors.

\ Please add new claims 20-33 as follows:

--20. A semiconductor device comprising:

ac a main semiconductor device having on a circuit-formation surface a plurality of power supply line connection pads and a plurality of ground line connection pads, conductors each of which is electrically connected to either one of said power supply connection pads or one of said ground line connection pads, respectively; and

capacitors electrically connected to at least one surface of said conductors; and

a flexible substrate comprising metal foil leads serving as said conductors and an insulation layer provided at least on a surface of said metal foil lead, said surface opposing said main semiconductor device, being joined to a circuit-formation surface of said main semiconductor device.--

--21. A semiconductor device according to claim 1, wherein said conductor is a lead.--

--22. A semiconductor device according to claim 1, wherein a plurality of first conductors are electrically connected to said power supply connection pads and a plurality of second conductors are electrically connected to said ground line connection pads; and

further wherein, said capacitors are electrically connected to one surface of said first conductor and connected to one surface of said second conductor.--

--23. A semiconductor device according to claim 20, wherein said capacitors function as decoupling capacitors suppressing or compensating for a momentary drop in a DC voltage supplied to said main semiconductor device.--

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--24. A semiconductor device according to claim 20, wherein said power supply line connection pads and said ground line connection pads are alternately disposed along an edge extension direction of a peripheral edge of said circuit-formation surface of said main semiconductor device, and that said capacitor is connected between two neighboring conductors each connected respectively to a power supply line connection pad and a ground line connection pad.--

--25. A semiconductor device according to claim 20, wherein either one of said power supply line connection pads or one of said ground line connection pads are connected to said conductor by a bump made of solder or gold.--

--26. A semiconductor device according to claim 20, wherein said insulation layer comprises a thermoplastic adhesive.--

--27. A semiconductor device according to claim 20, wherein said metal foil leads are formed on only a peripheral edge part of said circuit-formation surface of said main semiconductor device, a plurality of holes are provided on said insulation layer provided in a region formed on said circuit-formation surface of said main semiconductor device, and in said region, no metal foil lead is provided, and at positions corresponding to said plurality of pads of said main

semiconductor device, and a plurality of bumps of said main semiconductor device are caused to pass through each of said plurality of holes, thereby making joints to each of said plurality of pads.--

--28. A semiconductor device according to claim 22, wherein said capacitors function as decoupling capacitors suppressing or compensating for a momentary drop in a DC voltage supplied to said main semiconductor device.--

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--29. A semiconductor device according to claim 22, wherein said power supply line connection pads and said ground line connection pads are alternately disposed along an edge extension direction of a peripheral edge of said circuit-formation surface of said main semiconductor device, and that said capacitor be provided connected between two neighboring conductors each connected respectively to a power supply line connection pad and a ground line connection pad.--

--30. A semiconductor device according to claim 22, wherein either one of said power supply line connection pads or one of said ground line connection pads are connected to said conductor by a bump made of solder or gold.--

--31. A semiconductor device according to claim 22, wherein a flexible substrate comprising a metal foil lead serving as a conductor and an insulation layer provided at least on a surface of said metal foil lead, said surface opposing said main semiconductor device, is joined to a circuit-formation surface of said main semiconductor device.--

--32. A semiconductor device according to claim 22, wherein said insulation layer comprises a thermoplastic adhesive.--

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--33. A semiconductor device according to claim 22, wherein said metal foil leads are formed on only a peripheral edge part of said circuit-formation surface of said main semiconductor device, a plurality of holes are provided on said insulation layer provided in a region formed on said circuit-formation surface of said main semiconductor device, and in said region, no metal foil lead is provided, and at positions corresponding to said plurality of pads of said main semiconductor device, and a plurality of bumps of said main semiconductor device are caused to pass through each of said plurality of holes, thereby making joints to each of said plurality of pads.--

REMARKS

Objections to the drawings

The Examiner objected to the drawings as not showing a certain feature of claim 3.

The Examiner's attention is respectfully directed to Fig. 4 of the original drawings.

As seen from Fig. 4, metal foil leads 5 are mounted to insulation layer 3. Decoupling capacitors 2 straddle across each two neighboring metal foil leads and are connected thereto, (see specification, page 20, lines 1 to 9).

It is believed that in view of the above explanation the Examiner's objections to the drawings are avoided.